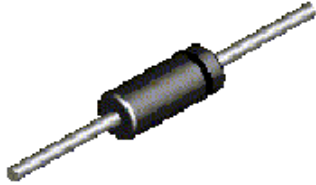


1N/FDLL 914/A/B / 916/A/B / 4148 / 4448



DO-35



LL-34

THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL.

COLOR BAND MARKING

| DEVICE | 1ST BAND | 2ND BAND |
|----------|----------|----------|
| FDLL914 | BLACK | BROWN |
| FDLL914A | BLACK | GRAY |
| FDLL914B | BROWN | BLACK |
| FDLL916 | BLACK | RED |
| FDLL916A | BLACK | WHITE |
| FDLL916B | BROWN | BROWN |
| FDLL4148 | BLACK | BROWN |
| FDLL4448 | BROWN | BLACK |

Small Signal Diode

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|--------------------|--------------------------------------------------------------------------------------------------------|-------------|-------|
| V _{RRM} | Maximum Repetitive Reverse Voltage | 100 | V |
| I _{F(AV)} | Average Rectified Forward Current | 200 | mA |
| I _{FSM} | Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond | 1.0 | A |
| | | 4.0 | A |
| T _{stg} | Storage Temperature Range | -65 to +200 | °C |
| T _J | Operating Junction Temperature | 175 | °C |

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

| Symbol | Characteristic | Max | Units |
|------------------|-----------------------------------------|-------------------------------|-------|
| | | 1N/FDLL 914/A/B / 4148 / 4448 | |
| P _D | Power Dissipation | 500 | mW |
| R _{θJA} | Thermal Resistance, Junction to Ambient | 300 | °C/W |

1N/FDLL 914/A/B / 916/A/B / 4148 / 4448

Small Signal Diode

(continued)

Electrical Characteristics T_A = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|-----------------|-----------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|----------------------------------------|------------------------------|
| V _R | Breakdown Voltage | I _R = 100 μA I _R = 5.0 μA | 100 75 | | V V |
| V _F | Forward Voltage | 1N914B/4448 I _F = 5.0 mA 1N916B I _F = 5.0 mA 1N914/916/4148 I _F = 10 mA 1N914A/916A I _F = 20 mA 1N916B I _F = 20 mA 1N914B/4448 I _F = 100 mA | 620 630 | 720 730 1.0 1.0 1.0 1.0 | mV mV V V V V |
| I _R | Reverse Current | V _R = 20 V V _R = 20 V, T _A = 150°C V _R = 75 V | | 25 50 5.0 | nA μA μA |
| C _T | Total Capacitance | 1N916A/B/4448 V _R = 0, f = 1.0 MHz 1N914A/B/4148 V _R = 0, f = 1.0 MHz | | 2.0 4.0 | pF pF |
| t _{rr} | Reverse Recovery Time | I _F = 10 mA, V _R = 6.0 V (60mA), I _{rr} = 1.0 mA, R _L = 100Ω | | 4.0 | ns |

1N/FD/L 914/A/B / 916/A/B / 4148 / 4448

Typical Characteristics

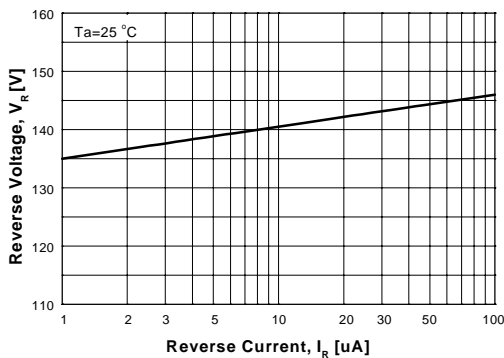


Figure 1. Reverse Voltage vs Reverse Current
BV - 1.0 to 100 uA

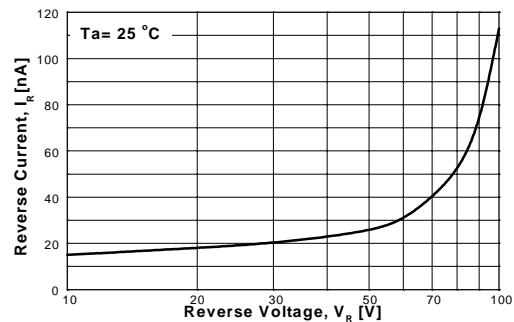


Figure 2. Reverse Current vs Reverse Voltage
IR - 10 to 100 V

GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

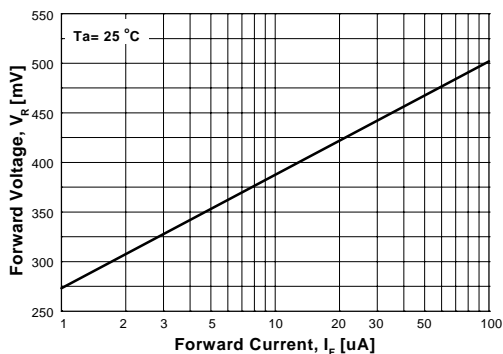


Figure 3. Forward Voltage vs Forward Current
VF - 1 to 100 uA

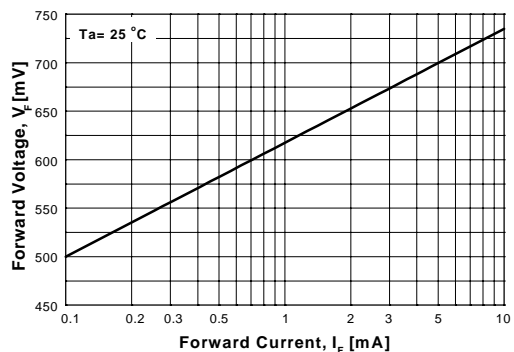


Figure 4. Forward Voltage vs Forward Current
VF - 0.1 to 10 mA

Typical Characteristics (continued)



Figure 5. Forward Voltage vs Forward Current
VF - 10 to 800 mA

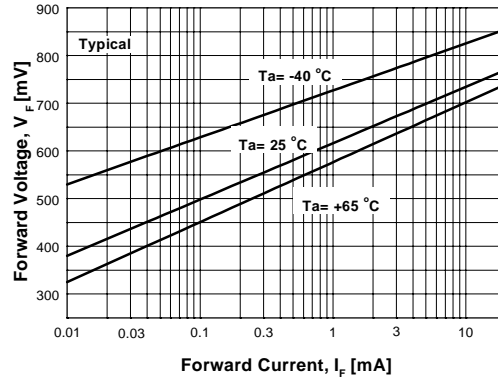


Figure 6. Forward Voltage
vs Ambient Temperature
VF - 0.01 - 20 mA (-40 to +65 Deg C)



Figure 7. Total Capacitance

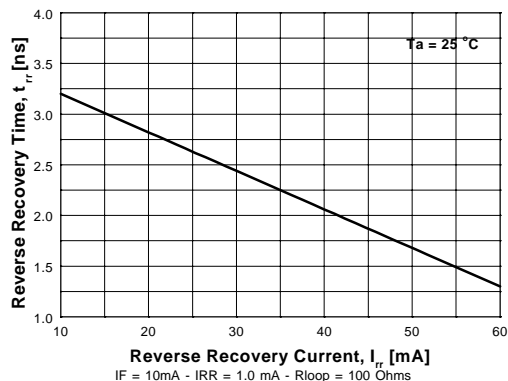


Figure 8. Reverse Recovery Time vs
Reverse Recovery Current

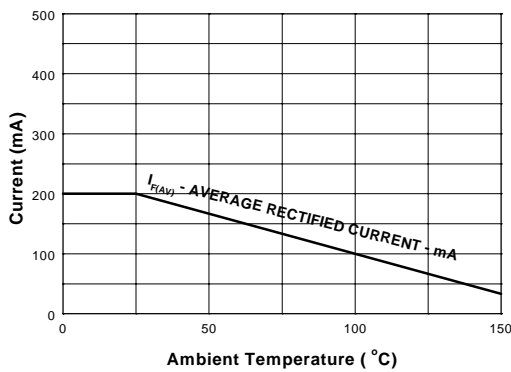


Figure 9. Average Rectified Current ($I_{F(AV)}$)
versus Ambient Temperature (T_A)

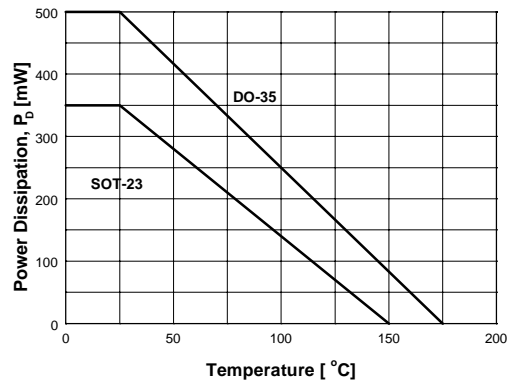


Figure 10. Power Derating Curve